



DGW20N65CTL0

RoHS
COMPLIANT

**Electrical Characteristics of the IGBT** $T_j = 25$ unless otherwise specified

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Collector-Emitter Breakdown Voltage	BV_{CES}	$V_{GE}=0V, I_C$	650		-	V
Gate Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=1mA$	5.0	5.8	6.5	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=20A$ $T_j=25^{\circ}C,$ $T_j=125^{\circ}C$ $T_j=150^{\circ}C$		1.60 1.75 1.80	1.95	V
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE}=600V, V_{GE}=0V$ $T_j=25^{\circ}C,$ $T_j=150^{\circ}C$			0.25 1.00	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE}=0V, V_{GE}=\pm 20V$			± 200	nA

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic						

Input Capacitance

 C_{ies}

V



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Electrical

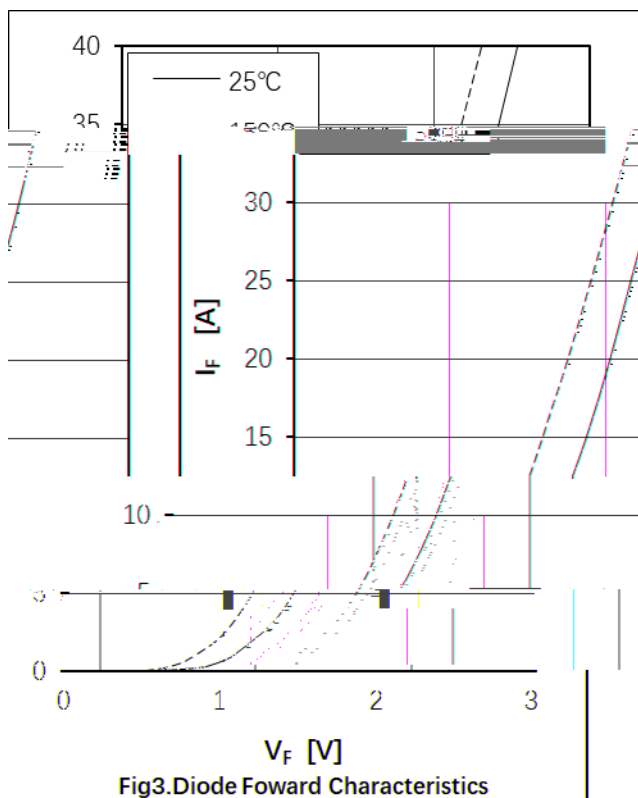
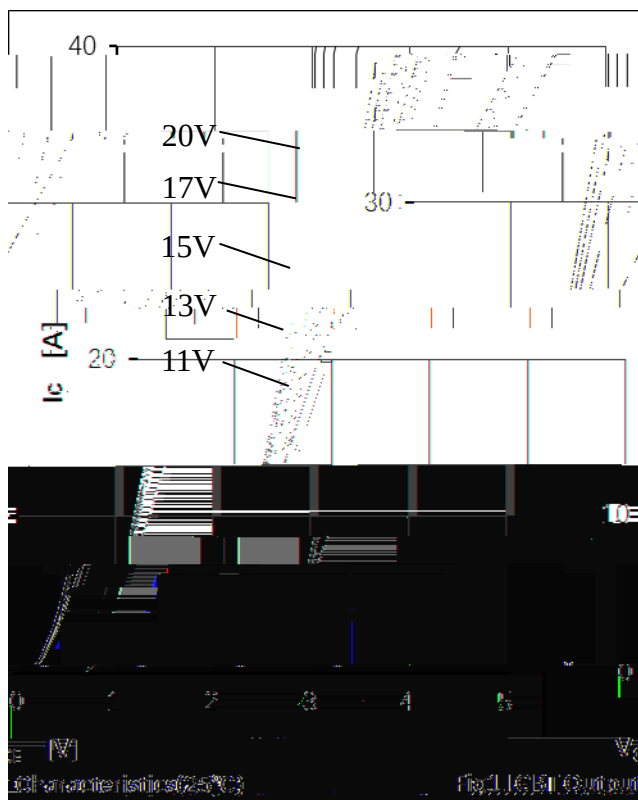


Fig3.Diode Foward Characteristics

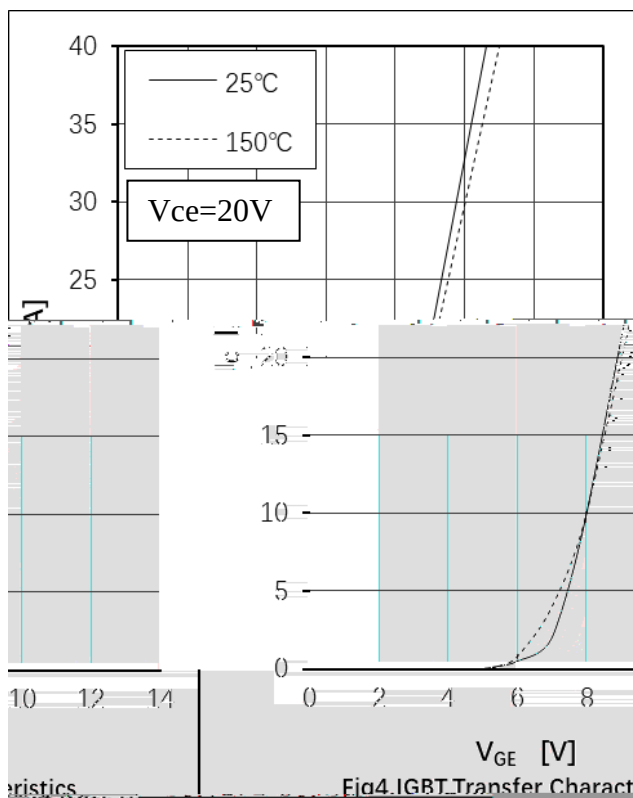
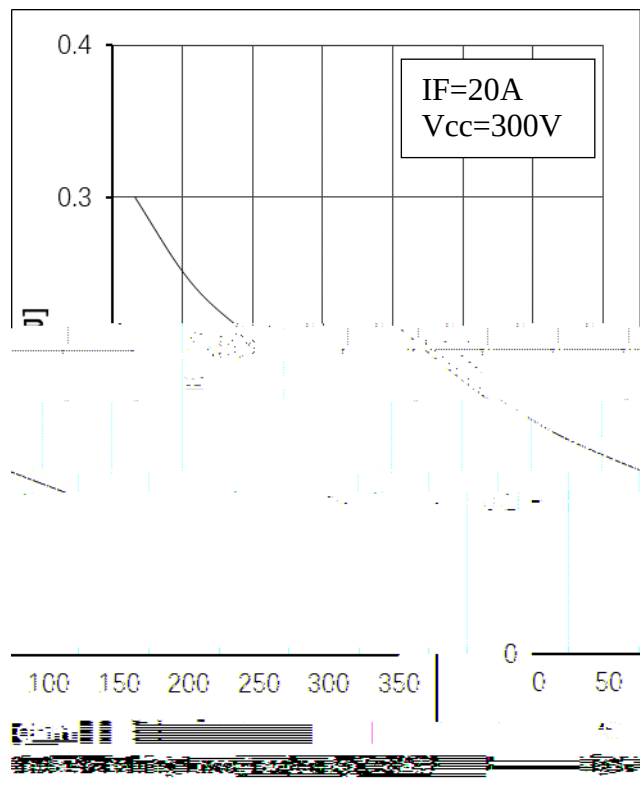
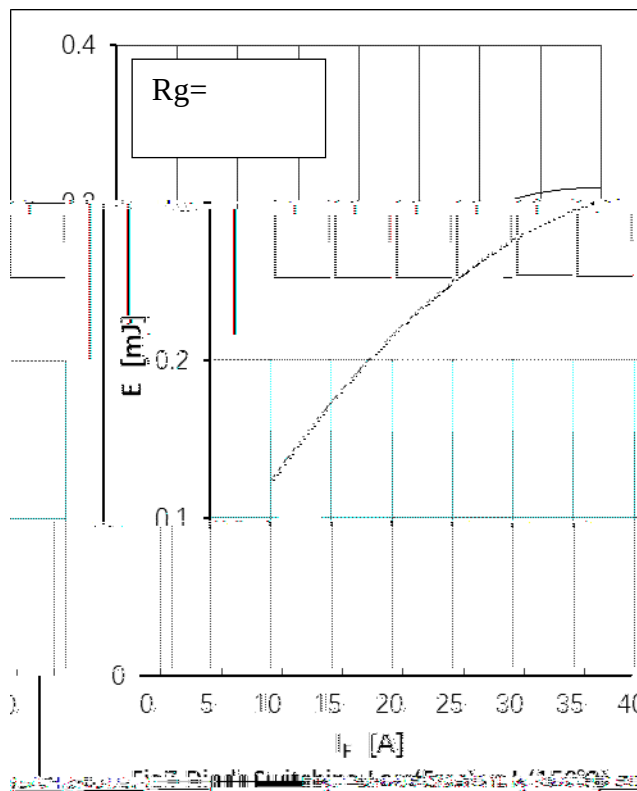
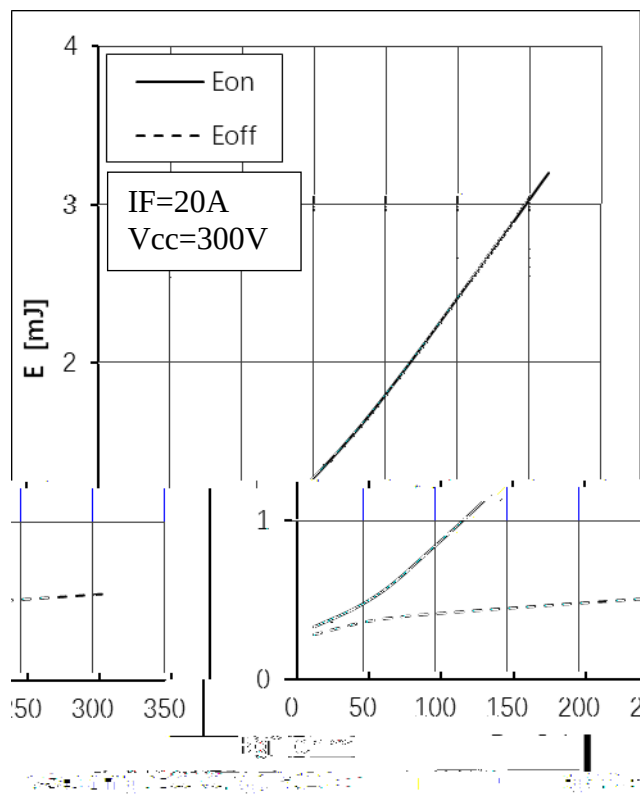
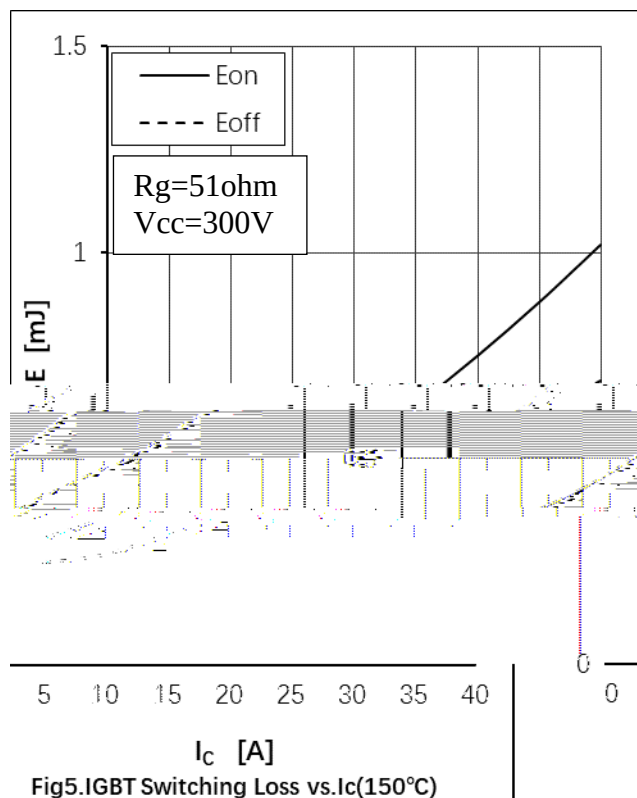
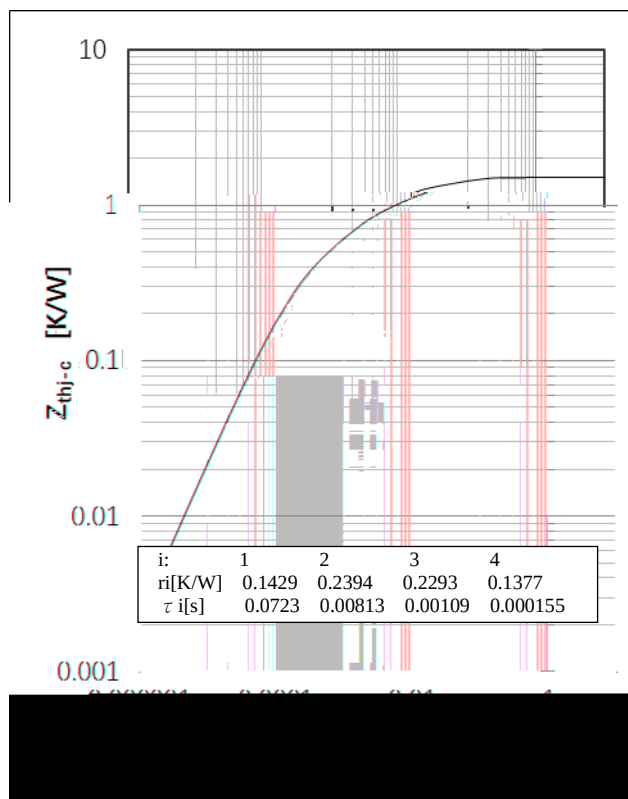
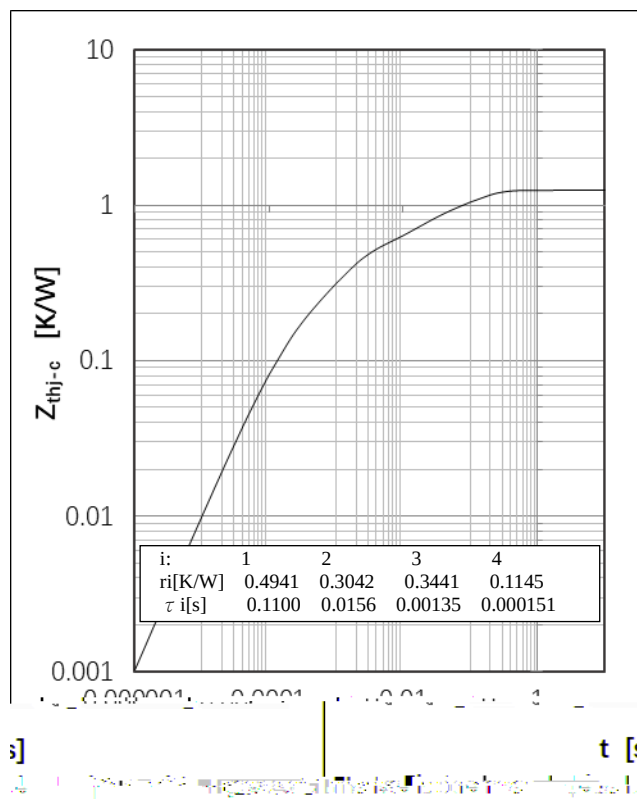
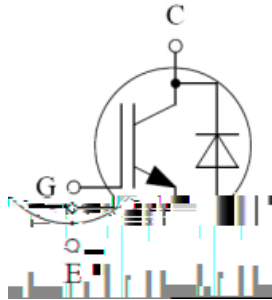


Fig4.IGBT Transfer Character







Package Outline Information

TO-247AB		
Dim	Min	